

FIG. 1

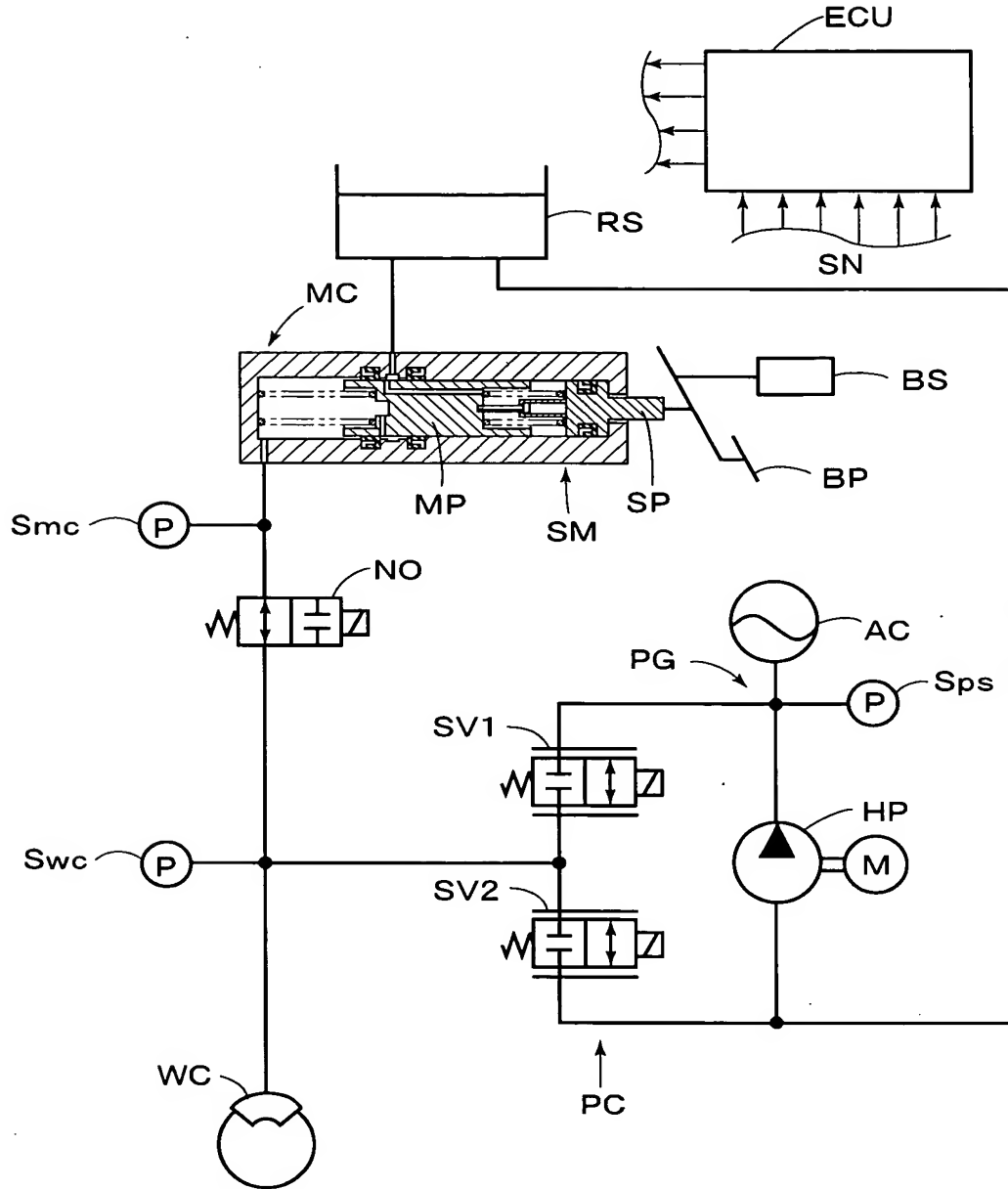




FIG. 3

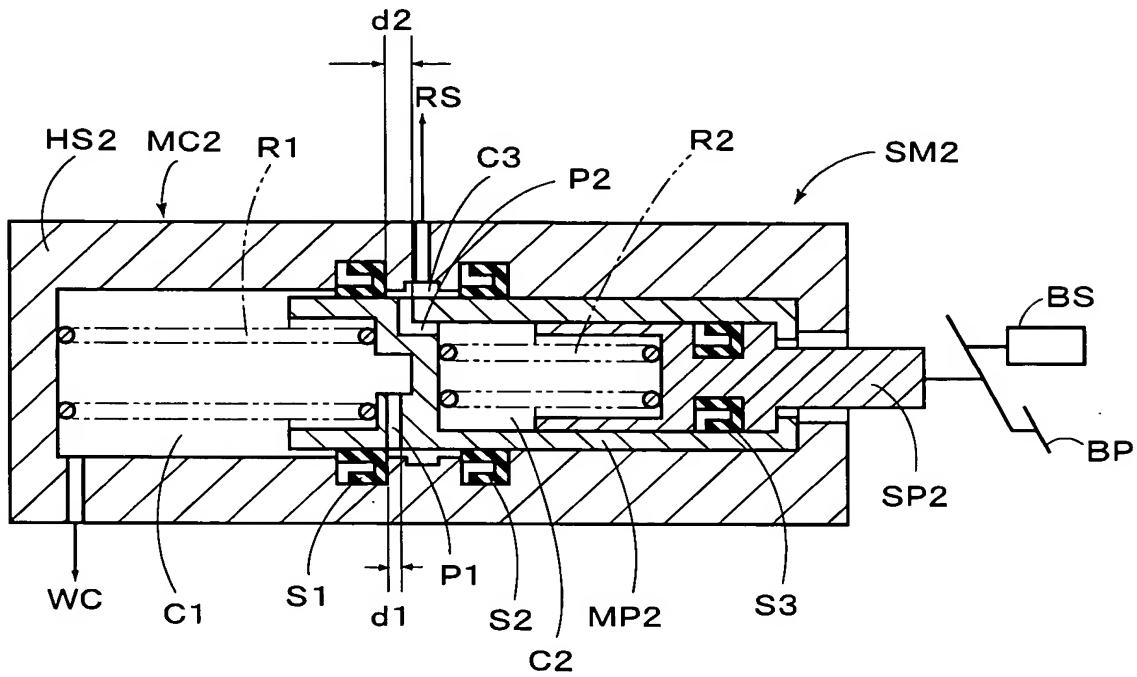


FIG. 4

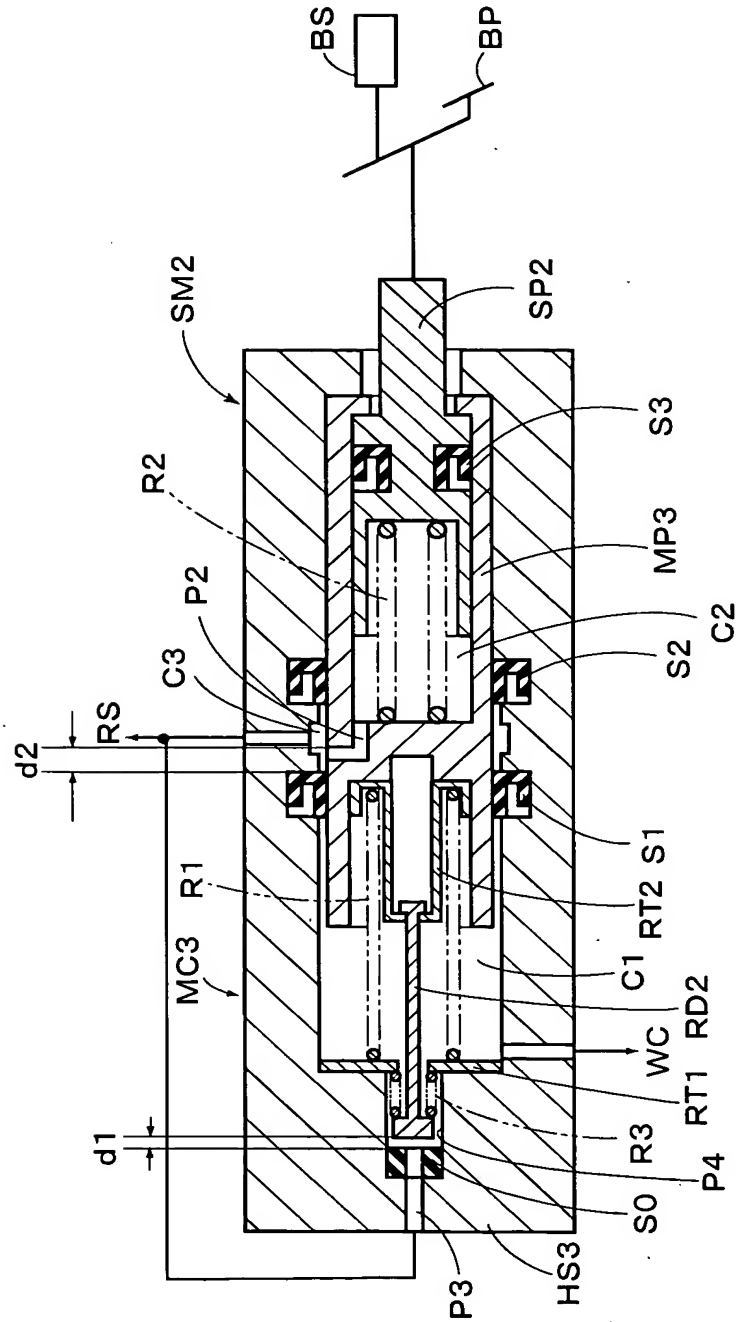
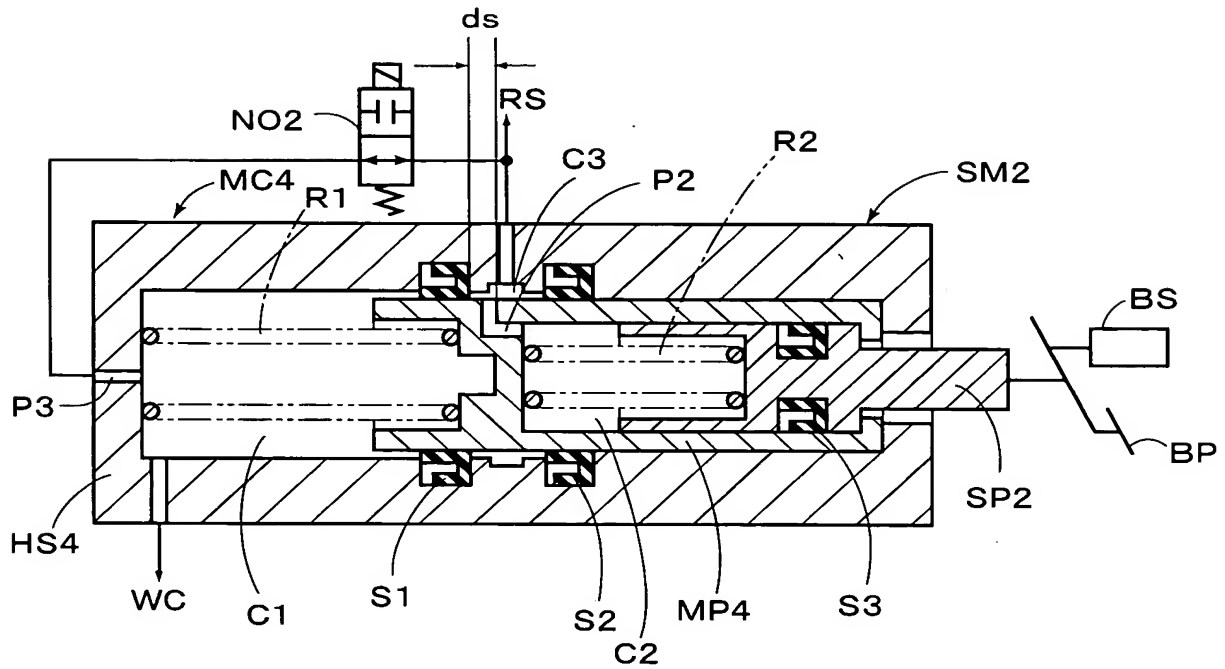


FIG. 5



A detailed cross-sectional view of a multi-layered device, likely a semiconductor or microfluidic component. The device consists of several layers and internal structures. Key components and labels include:

- WC**: A layer at the bottom left.
- C1**: A layer above WC.
- S4**: A layer above C1.
- d1**: A dimension indicating the thickness of S4.
- P1**: A layer above S4.
- S5**: A layer above P1.
- P5**: A layer above S5.
- C5**: A layer above P5.
- S1**: A layer above C5.
- MP5**: A layer above S1.
- S2**: A layer above MP5.
- RD**: A layer above S2.
- C2**: A layer above RD.
- S3**: A layer above C2.
- SP**: A layer above S3.
- BP**: A layer above SP.
- BS**: A layer above BP.
- MC5**: A layer on the left side.
- R1**: A layer above MC5.
- RS**: A layer above R1.
- C4**: A layer above RS.
- C3**: A layer above C4.
- P2**: A layer above C3.
- R2**: A layer above P2.
- RT**: A layer above R2.
- SM**: A layer above RT.
- d2**: A dimension indicating the thickness of the top layer.

The diagram shows various internal features, including holes, channels, and interfaces between different materials or layers.